



# LAPD-2-09-17-CHIP

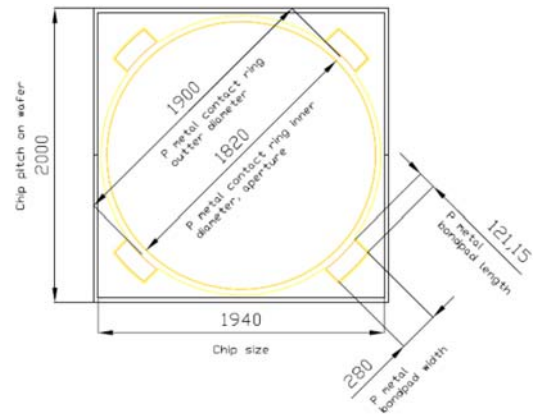


## TECHNICAL DATA

### Photodiode Chip die

### InGaAs

LAPD-2-09-17-CHIP adopt InGaAs pin structure based on InP by MOCVD method and planar diffusing technology. The active area is Ø 2 mm respectively.



### Absolute Maximum Ratings

Item	Symbol	Value	Unit
Reverse Voltage	$U_R$	20	V
Reverse Current	$I_R$	20	mA
Forward current	$I_F$	10	mA
Operating Temperature	$T_{opr}$	-20 ... +85	°C
Storage Temperature	$T_{stg}$	-40 ... +85	°C

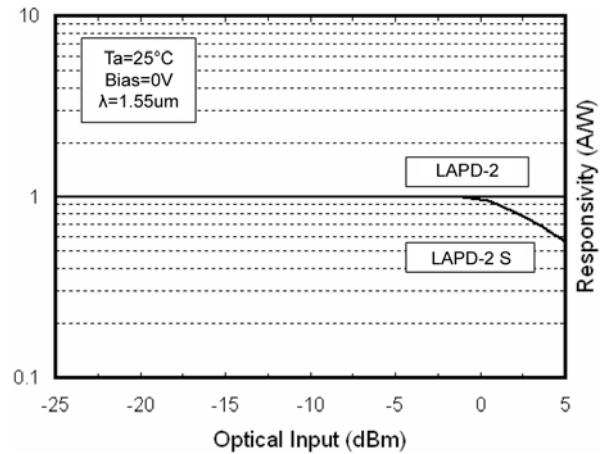
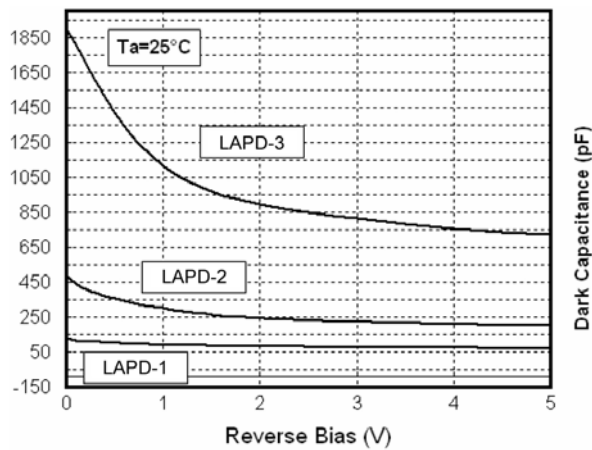
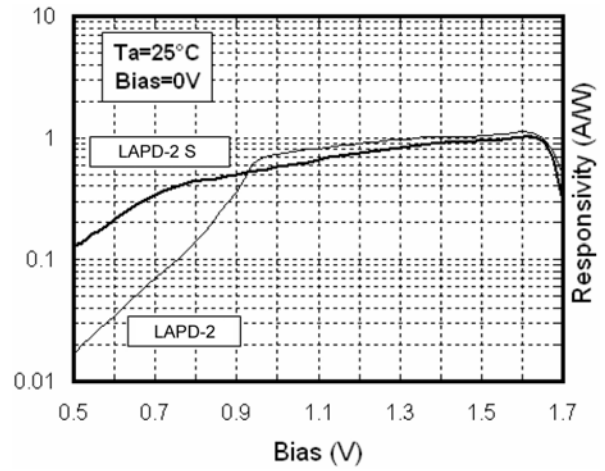
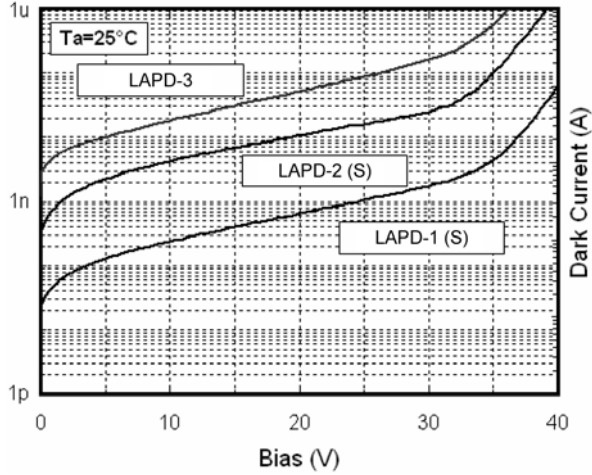
### Specifications

Item	Min.	Typ.	Max.	Unit
Wavelength Range	0.9 .. 1.7			µm
Active Area	Ø 2			mm
Saturation Power	1550 nm	-	2	dBm
Specific Detectivity ( $D^*$ )	1550 nm	2.5	5	$10^{12}$ Jones
Responsibility (0 V)	650 nm	0.02	0.05	A/W
	850 nm	0.10	0.20	
	1310 nm	0.80	0.90	
	1550 nm	0.85	0.95	
Capacitance	0 V	-	500	pF
	-5 V	-	250	
Dark Current	-5 V	-	10	nA
Shunt Resistance	6	25	-	MΩ
Chip Size	1940 x 1940			µm
Chip Thickness	300			µm

**Packing:** Chips on adhesive film



## Typical Performance Curves



LAPD-2 Spatial Response  
Ta=25°C, Bias=0V, λ=1550nm

